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1700 MHz to 2200 MHz 1 WATT POWER AMP



Package: Exposed Pad SOIC-8

WITH ACTIVE BIAS



Product Description

RFMD's SPA2318Z is a high efficiency GaAs Heterojunction Bipolar Transistor (HBT) amplifier housed in a low-cost surface-mountable plastic package. These HBT amplifiers are fabricated using molecular beam epitaxial growth technology which produces reliable and consistent performance from wafer to wafer and lot to lot. This product is specifically designed for use as a driver amplifier for infrastructure equipment in the 1960MHz and 2140MHz bands. Its high linearity makes it an ideal choice for multi-carrier and digital applications. The matte tin finish on the lead-free package utilizes a post annealing process to mitigate tin whisker forma-

 Optimum Technology Matching® Applied
 pac that

 ✓
 GaAs HBT
 dan

 ✓
 GaAs MESFET
 dan

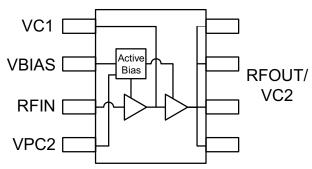
 InGaP HBT
 siGe BicMOS
 siGe BicMOS

 SiGe BicMOS
 SiGe HBT
 dan

 GaAs pHEMT
 Si CMOS
 si CMOS

 Si BJT
 GaN HEMT
 RF MEMS

tion and is RoHS compliant per EU Directive 2002/95. This package is also manufactured with green molding compounds that contain no antimony trioxide or halogenated fire retardants.



Features

- High Linearity Performance: +21dBm IS-95 Channel Power at -55dBc ACP; +20.7dBm WCDMA Channel Power at -50dBc ACP; +47dBm Typ. OIP₃
- On-Chip Active Bias Control
- High Gain: 24dB Typ. at 1960MHz
- Patented High Reliability GaAs HBT Technology
- Surface-Mountable Plastic Package

Applications

- WCDMA Systems
- PCS Systems
- Multi-Carrier Applications

Parameter	Specification			Unit	Condition	
Parameter	Min.	Тур.	Max.	Unit	Condition	
Frequency of Operation	1700		2200	MHz		
Output Power at 1dB Compression [1]		29.5		dBm	1960MHz	
\sim		29.5		dBm	2140MHz	
Adjacent Channel Power ^[1]		-55.0		dBc	1960MHz, IS-95 at P _{OUT} =21.0dBm, WCDMA at P _{OUT} =20.7dBm	
		-50.0	-47.0	dBc	2140MHz	
Small Signal Gain ^[1,2]		24.0		dB	1960MHz	
	21.0	23.5	24.5	dB	2140MHz	
Input VSWR ^[1,2]		1.6:1			1960MHz	
		1.6:1			2140MHz	
Output Third Order Intercept Point ^[2]		46.5		dBm	1960MHz, Power out per tone=+14dBm	
		47.0		dBm	2140MHz	
Noise Figure ^[1,2]		5.5		dB	1960MHz	
		5.5		dB	2140MHz	
Device Current ^[1,2]	360	400	425	mA	I _{BIAS} =10mA, I _{C1} =70mA, I _{C2} =320mA	
Device Voltage ^[1,2]	4.75	5.0	5.25	V		
Thermal Resistance (Junction - Lead)		31		°C/W	T _L =85°C	

Test Conditions: $Z_0=50\Omega$ Temp=25°C $V_{CC}=5.0V$ [1] Optimal ACP tune [2] Optimal IP₃ tune

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SPA2318Z



Absolute Maximum Ratings

Parameter	Rating	Unit			
Max Supply Current (I _{C1}) at V _{CC} typ.	150	mA			
Max Supply Current (I _{C2}) at V _{CC} typ.	750	mA			
Max Device Voltage (V $_{\rm CC}$) at I $_{\rm CC}$ typ.	6.0	V			
Max RF Input Power	16	dBm			
Max Junction Temp (T_J)	+160	°C			
Max Storage Temp	+150	°C			
Moisture Sensitivity Level	3	MSL			

Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one. Bias Conditions should also satisfy the following expression:

 $I_D V_D < (T_J - T_L) / R_{TH}$, j-l



Caution! ESD sensitive device.

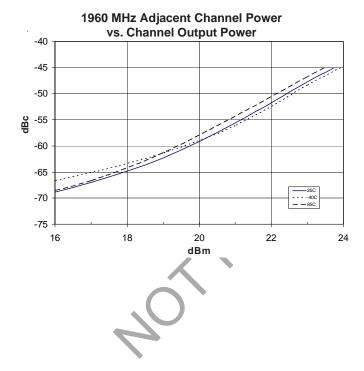
Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical perfor-mance or functional operation of the device under Absolute Maximum Rating condi-tions in substantiation of the device and the second se tions is not implied.

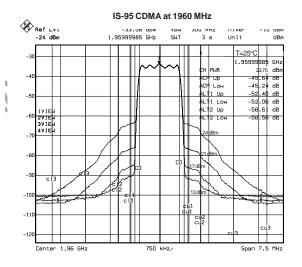
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RFMD Green: RoHS compliant per EU Directive 2002/95/EC, halogen free per IEC 61249-2:21, < 1000 ppm each of antimony trioxide in polymeric materials and red phosphorus as a flame retardant, and <2% antimony in solder.



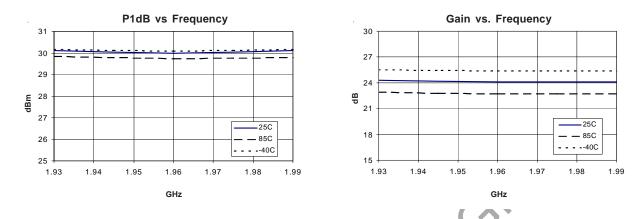




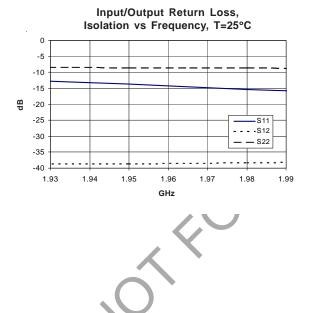


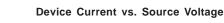


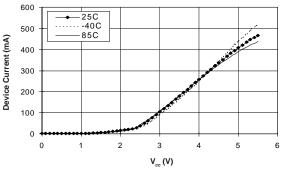
ACP Optimized 1960MHz Application Circuit Data, I_{CC}=400mA, V_{CC}=5V



ACP Optimized 1960MHz Application Circuit Data, I_{CC} =400mA, V_{CC} =5V

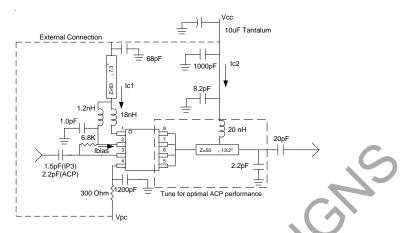




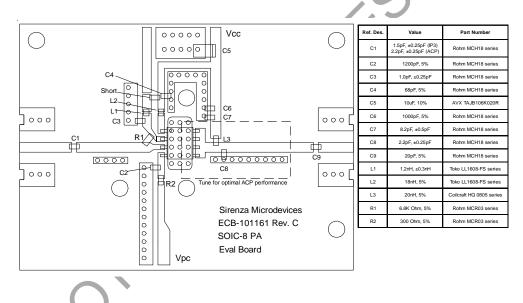




1930 MHz to 1990 MHz Application Schematic



1930 MHz to 1990 MHz Evaluation Board Layout and Bill of Materials

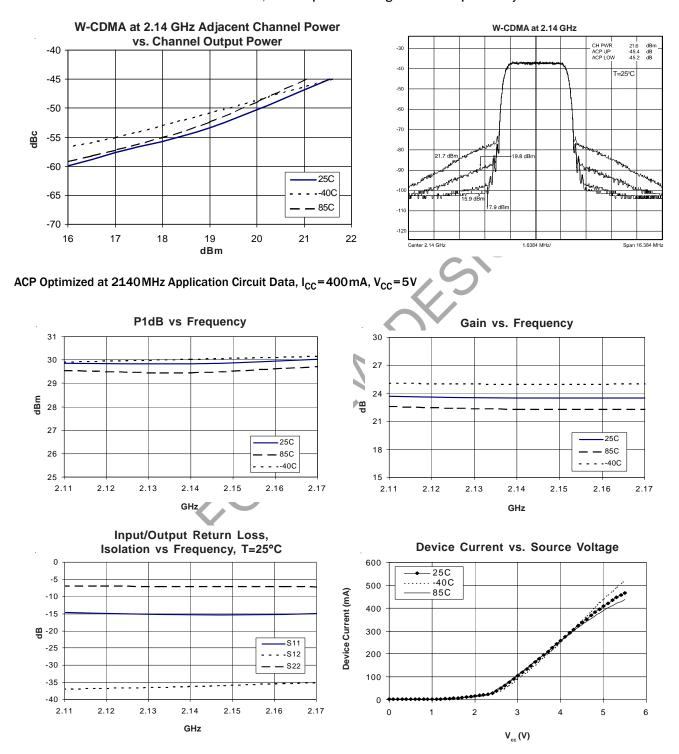


ACP Optimized 2140MHz Application Circuit Data, I_{CC} =400mA, V_{CC} =5V IS-95, WCDMA setup is



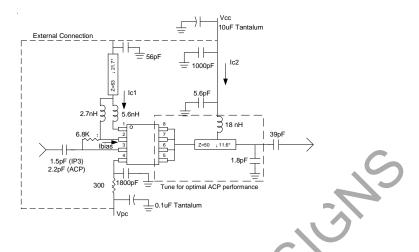


PCCPCH+PSCH+SSCH+CPICH+PICH+64DPCH, 10.5dB peak to average at 0.001% probability

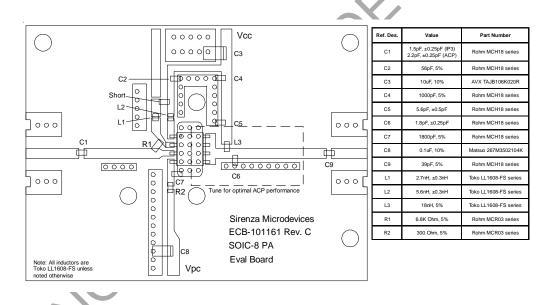








2110 MHz to 2170 MHz Evaluation Board Layout and Bill of Materials

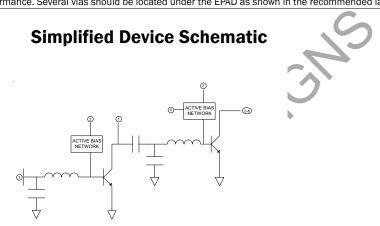


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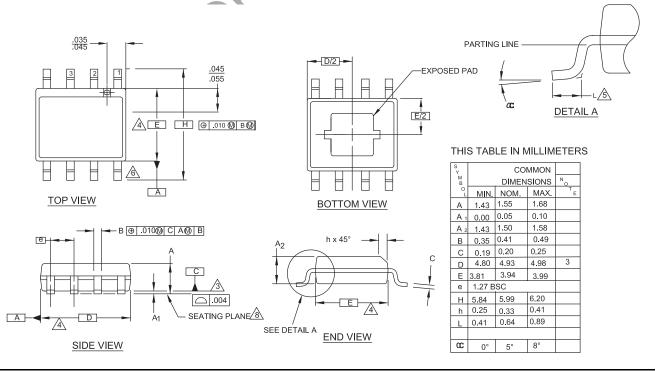
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Pin	Function	Description	
1	VC1	VC1 is the supply voltage for the first stage transistor. The configuration as shown on the Application Schematic is required for optimum RF performance.	
2	VBIAS	VBias is the bias control pin for the active bias network. Recommended configuration is shown in the Application Sche- matic.	
3	RF IN	RF input pin. This pin requires the use of an external DC blocking capacitor as shown in the Application Schematic.	
4	VPC2	VPC2 is the bias control pin for the active bias network for the second stage. The recommended configuration is shown in the Application Schematic.	
5, 6,	RF OUT / VC2	RF output and bias pins. Bias should be supplied to this pin through an external RF choke. Because DC biasing is pres on this pin, a DC blocking capacitor should be used in most applications (see Application Schematic). The supply side	
7, 8		the bias network should be well bypassed. An output matching network is necessary for optimum performance.	
EPAD	GND	Exposed area on the bottom side of the package needs to be soldered to the ground plane of the board for thermal and RF performance. Several vias should be located under the EPAD as shown in the recommended land pattern.	



Package Drawing

Dimensions in inches (millimeters) Refer to drawing posted at www.rfmd.com for tolerances.





Branding Diagram

